

# MA3X704D, MA3X704E

Silicon epitaxial planar type

For switching circuits

For wave detection circuit

■ Features

- Two MA3X704As are contained in one package
- Low forward rise voltage ( $V_F$ ) and satisfactory wave detection efficiency ( $\eta$ )
- Small temperature coefficient of forward characteristic
- Extremely low reverse current  $I_R$

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

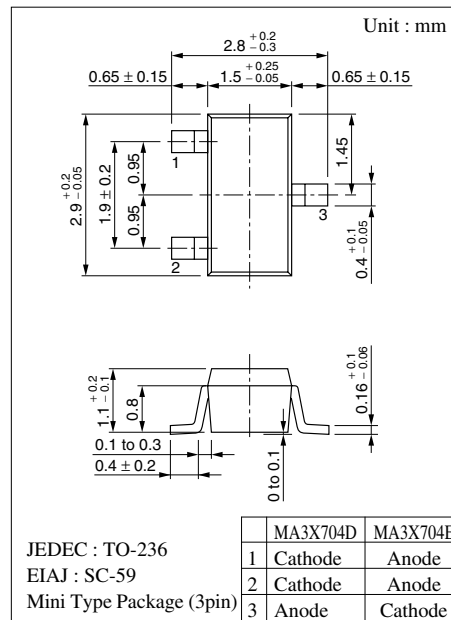
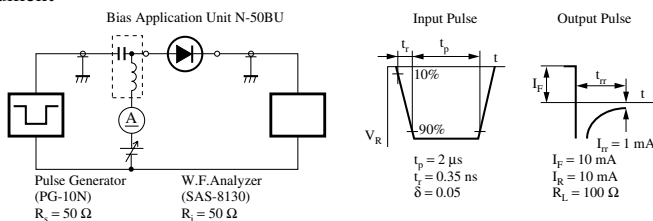
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	MA3X704D/E $V_R$	30	V
Peak forward current	Single	150	mA
	Double*		
Forward current (DC)	Single	30	mA
	Double*		
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note) \* : Value per chip

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 30\text{ V}$			1	$\mu\text{A}$
Forward voltage (DC)	$V_{F1}$	$I_F = 1\text{ mA}$			0.4	V
		$I_F = 30\text{ mA}$			1.0	V
Terminal capacitance	$C_t$	$V_R = 1\text{ V}, f = 1\text{ MHz}$		1.5		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 10\text{ mA}$ $I_{rr} = 1\text{ mA}, R_L = 100\ \Omega$		1.0		ns
Detection efficiency	$\eta$	$V_{in} = 3\text{ V}_{(peak)}, f = 30\text{ MHz}$ $R_L = 3.9\text{ k}\Omega, C_L = 10\text{ pF}$		65		%

- Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment
2. Rated input/output frequency: 2 000 MHz
3. \* :  $t_{rr}$  measuring instrument



Marking Symbol

- MA3X704D : M2P
  - MA3X704E : M2R
- Internal Connection

